

GDMA77 SURFACE MOUNT, BAND SWITCHING DIODE

VOLTAGE 35V, CURRENT 0.1A

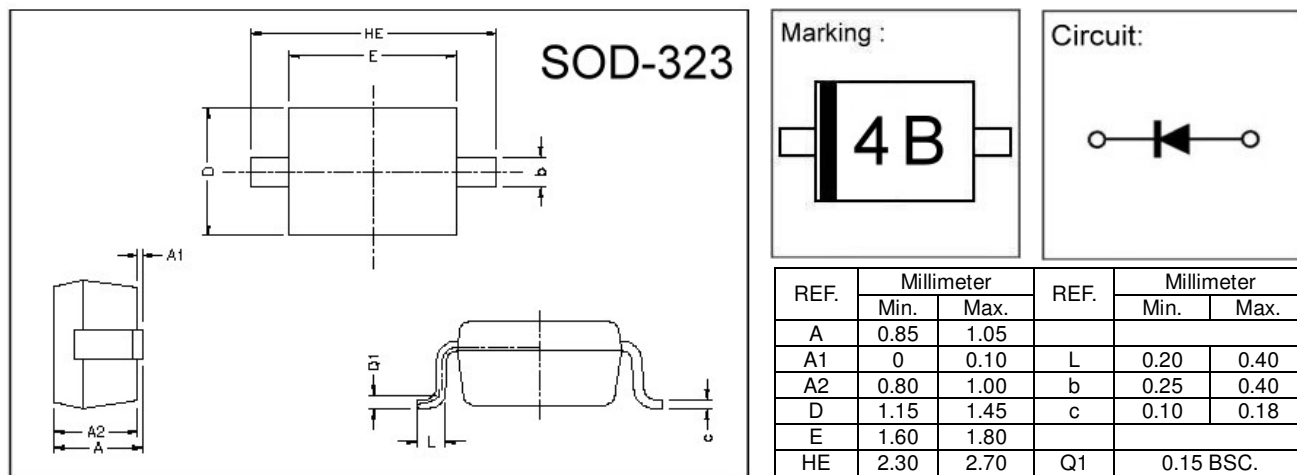
Description

The GDMA77 is designed for band switching application.

Features

- Low forward dynamic resistance r_f
- Less voltage dependence of diode capacity C_D

Package Dimensions



Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

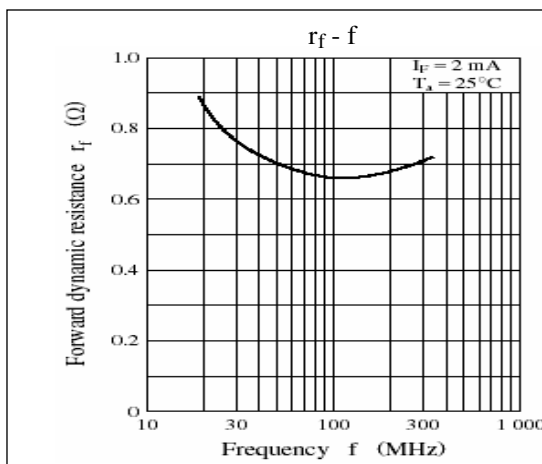
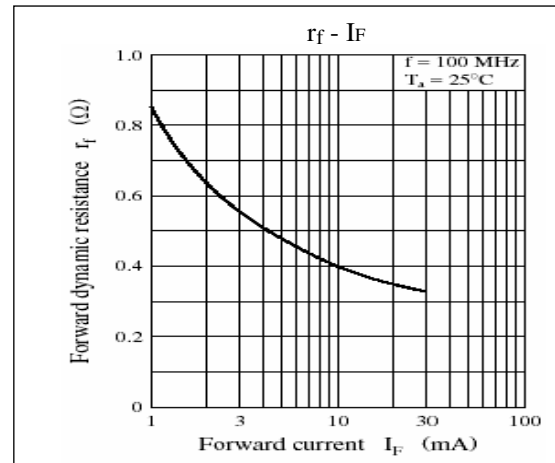
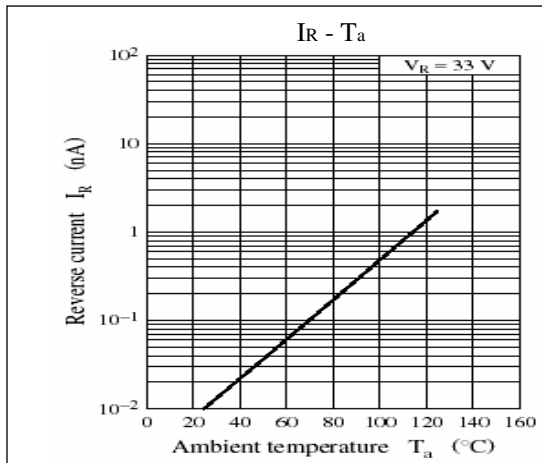
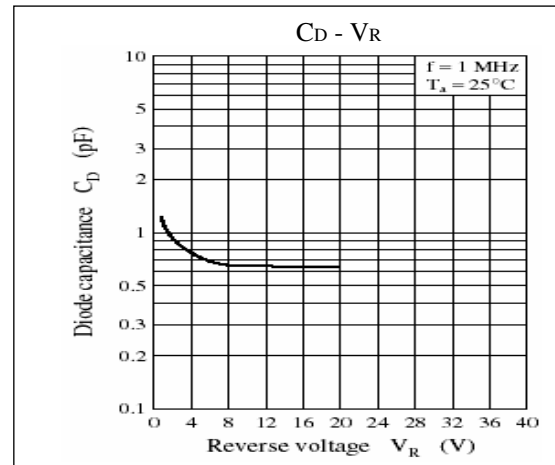
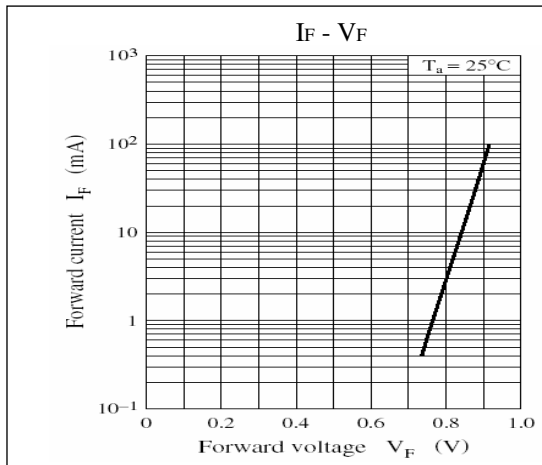
Parameter	Symbol	Ratings	Unit
Reverse Voltage(DC)	V_R	35	V
Forward Current(DC)	I_F	100	mA
Junction Temperature	T_j	+125	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 ~ +150	$^\circ\text{C}$
Total Power Dissipation	P_D	225	mW

Electrical Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Reverse Breakdown	V_R	35	-	-	V	$I_R=10\mu\text{A}$
Reverse Current(DC)	I_R	-	0.01	100	nA	$V_R=33\text{V}$
Reverse Voltage(DC)	V_F	-	0.92	1	V	$I_F=100\text{mA}$
Diode Capacitance	C_D	-	0.9	1.2	pF	$V_R=6, f=1\text{MHz}$
Forward dynamic resistance	r_f	-	0.65	0.85	Ω	$I_F=2\text{mA}, f=100\text{MHz}$

Note 1: Rated input/output frequency: 100MHz

Characteristics Curve



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